

NCE Automotive P-Channel Enhancement Mode Power MOSFET

Description

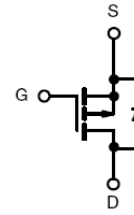
The NCEA60P28AK uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for high current load applications.

General Features

- $V_{DS} = -60V, I_D = -28A$
 $R_{DS(ON)} < 48m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- 100% UIS tested
- 100% ΔV_{ds} tested
- **AEC-Q101 qualified**

Application

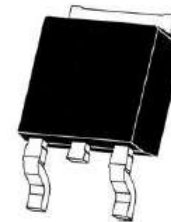
- Automotive application
- High side switch for full bridge converter
- DC/DC converter for LCD display



Schematic diagram



Marking and pin assignment



TO-252 -2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A60P28AK	NCEA60P28AK	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-28	A
	$I_D(100^\circ C)$	-19.8	A
Pulsed Drain Current	I_{DM}	-112	A
Maximum Power Dissipation	P_D	80	W
Derating factor		0.53	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	100	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.88	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	40	48	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	48	55	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	-	10	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{ISS}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	1630.7	-	pF
Output Capacitance	C _{OSS}		-	90.6	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	77.3	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =1.5Ω, V _{GS} =-10V, R _G =3Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Q _g	V _{DS} =-30V, I _D =-20A, V _{GS} =-10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	3.4	-	nC
Gate-Drain Charge	Q _{gd}		-	6.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-20A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-18	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = -20A	-	34	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = -100A/μs (Note 3)	-	37	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: T_j=25°C, V_{DD}=-30V, V_G=-10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics (Curves)

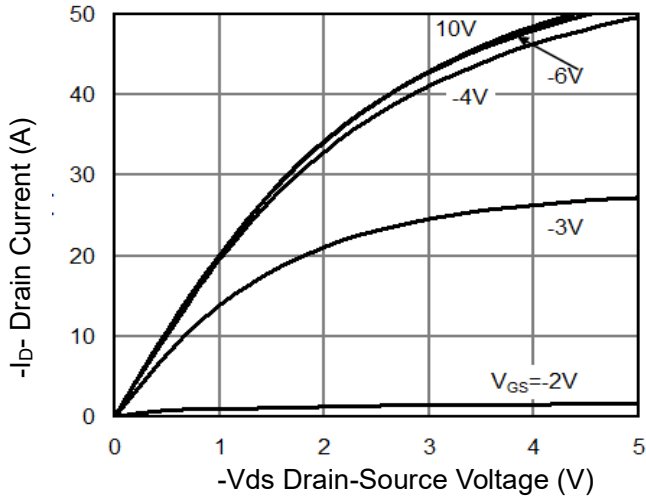


Figure 1 Output Characteristics

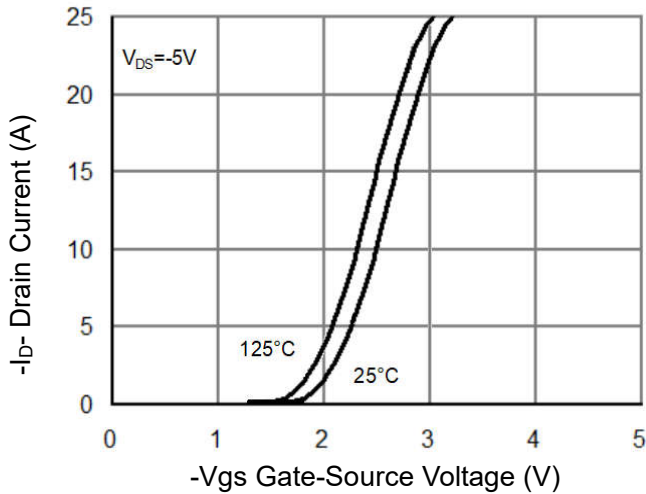


Figure 2 Transfer Characteristics

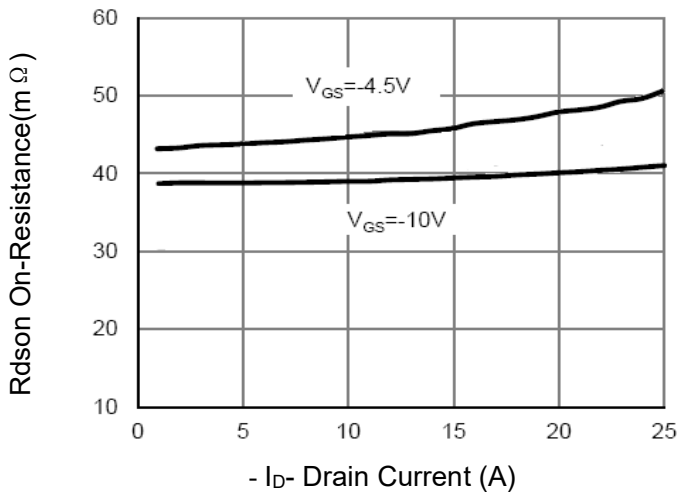


Figure 3 $R_{DS(on)}$ - Drain Current

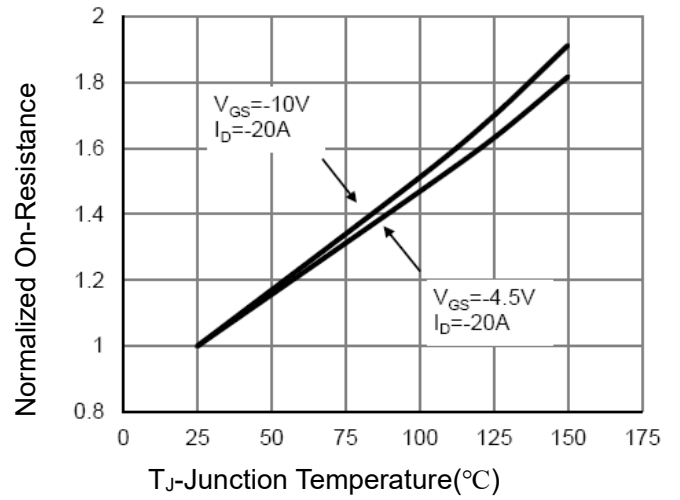


Figure 4 $R_{DS(on)}$ -Junction Temperature

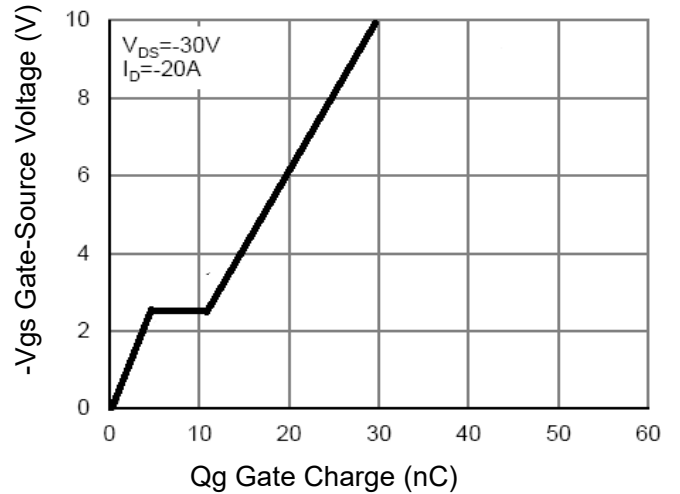


Figure 5 Gate Charge

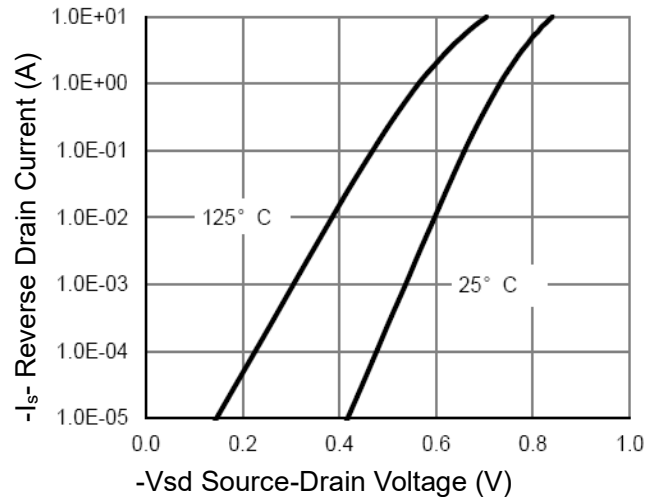


Figure 6 Source- Drain Diode Forward

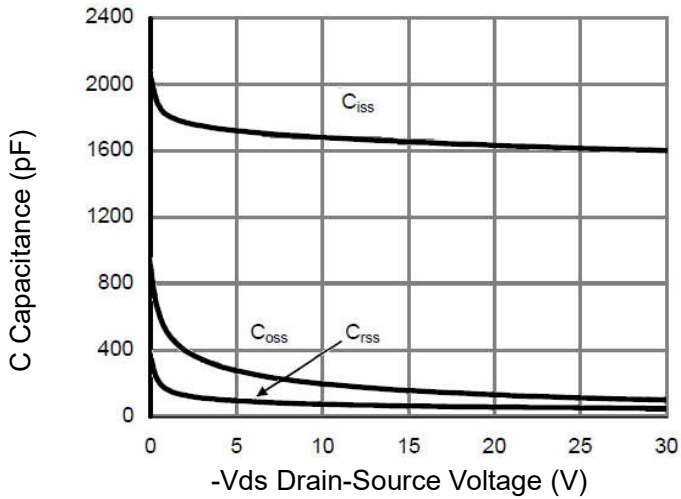


Figure 7 Capacitance vs Vds

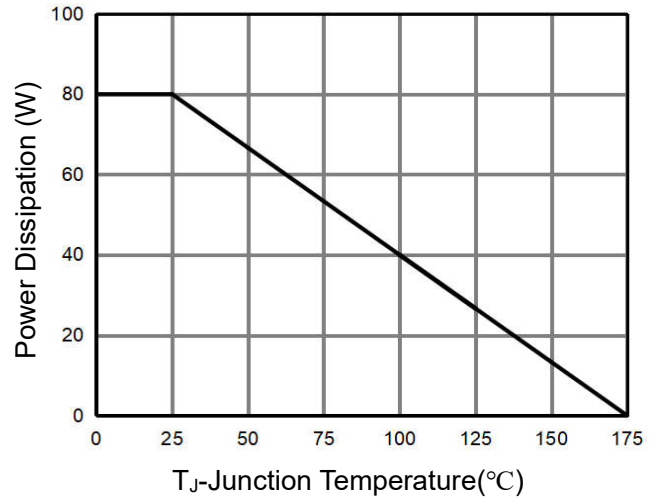


Figure 9 Power De-rating

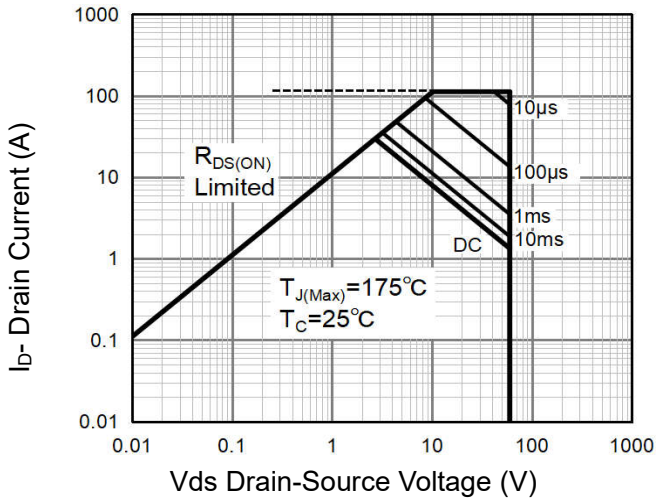


Figure 8 Safe Operation Area

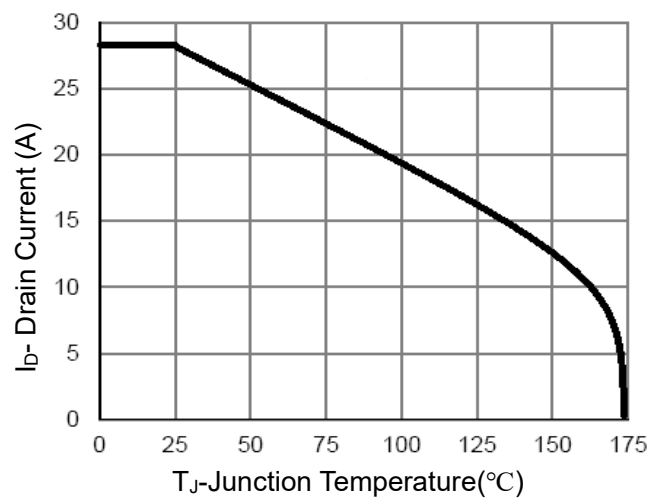


Figure 10 ID Current De-rating

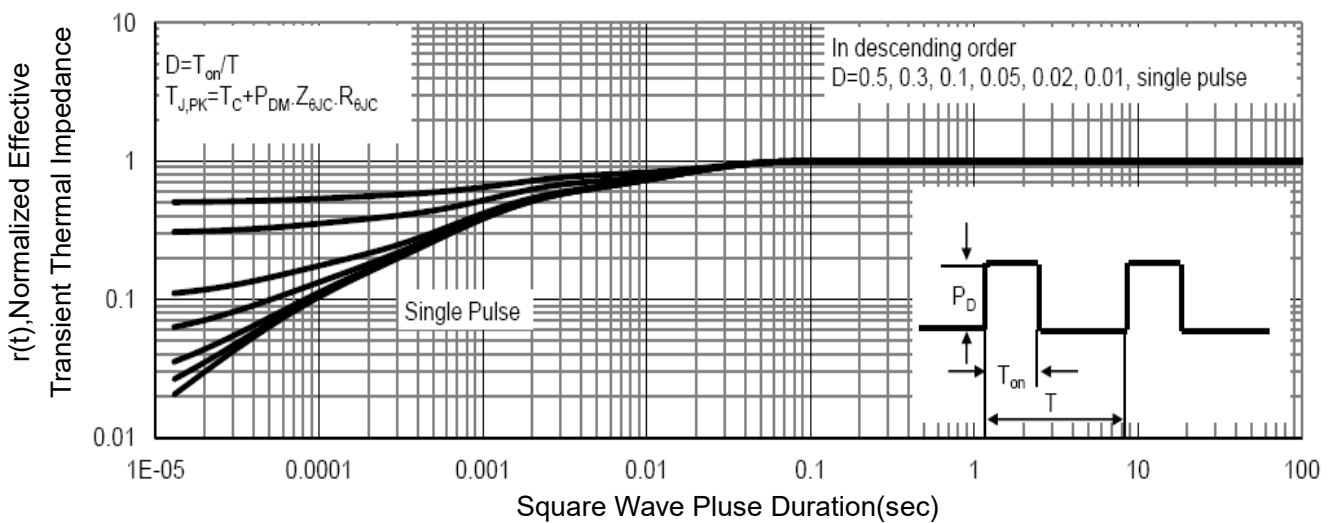
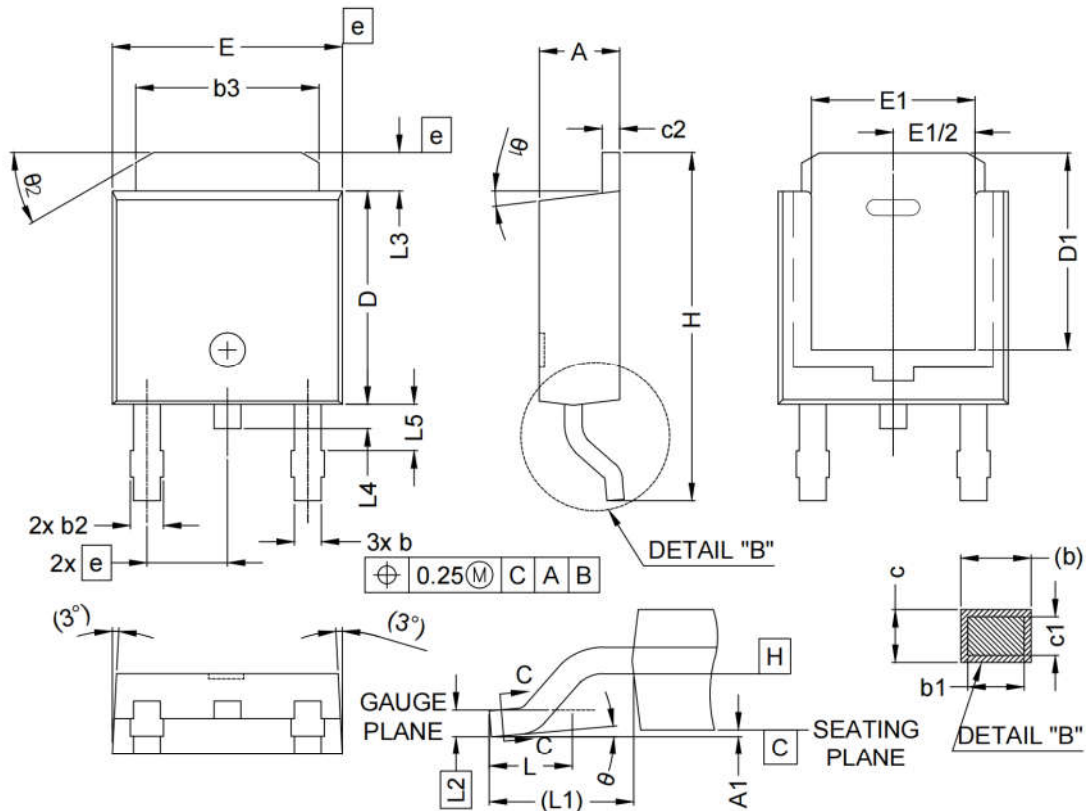


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	2.18	2.39	E	6.35	6.73	θ_1	0°	15°
A1	-	0.13	E1	4.32	-	θ_2	25°	35°
b	0.65	0.89	e	2.29 BSC				
b1	0.64	0.79	H	9.94	10.34			
b2	0.76	1.13	L	1.50	1.78			
b3	4.95	5.46	L1	2.74 REF				
c	0.46	0.61	L2	0.51 BSC				
c1	0.41	0.56	L3	0.89	1.27			
c2	0.46	0.60	L4	-	1.02			
D	5.97	6.22	L5	1.14	1.49			
D1	5.21	-	θ	0°	10°			

NOTE ; 1.0 DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
 2.0 ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
 3.0 HEAT SINK SIDE FLASH IS MAX. 0.8mm.
 4.0 RADIUS ON TERMINAL IS OPTIONAL.

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